PW022N08CBS

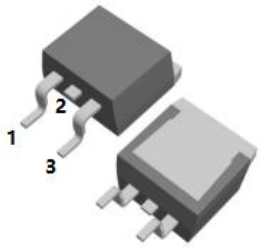
MOSFET

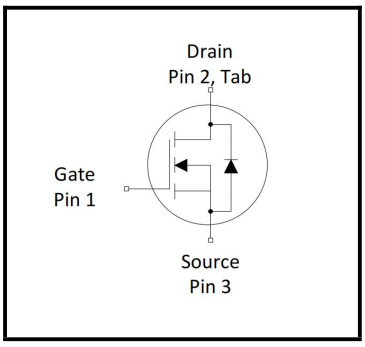
180 Amps,80 Volts N-CHANNEL MOSFET

FEATURE

- Low gate charge
- Low Ciss
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS 2.0 Compliant

TO-263CB-2L





Parameter	Values	Unit
Bvdss	80	V
Id	180	A
Rdson(max)	2.2	mΩ

Ordering Code	Marking	Package	Packaging
PW022N08CBS	PW022N08CBS	TO-263CB-2L	Tape and reel

Absolute Maximum Ratings(T_C=25℃,unless otherwise noted)

Parameter	Symbol	Values			Unit	Note/Test Conditions
		Min	Typ	Max		
Drain-Source Voltage	V_{DSS}	-	-	80	V	-
Gate-Source Voltage	V_{GS}	-20	-	20	V	-
Continuous Drain Current(Package Limited)	I_D	-	-	180	A	T_C=25℃
		-	-	90	A	T_C=100℃
Pulsed Drain Current(Note1)	I_{DM}	-	-	720	A	-
Single Pulse Avalanche Energy	E_{AS}	-	-	529	mJ	L=0.5mH,V_D=80V, T_C=25℃
Maximum Power Dissipation	P_D	-	-	227	W	T_C=25℃
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55	-	150	℃	-
Maximum lead temperature for soldering purposes, 1/8"from case for 5 seconds	T_L	-	-	260	℃	-

Thermal Characteristics

Parameter	Symbol	Values			Unit	Note/Test Conditions
		Min	Typ	Max		
Thermal resistance , Channel to Case	$R_{th(ch-c)}$	-	-	0.55	℃/W	-

Electrical Characteristics (T_C=25℃,unless otherwise noted)

Static characteristics

Parameter	Symbol	Values			Unit	Note/Test Conditions
		Min	Typ	Max		
Drain-Source Breakdown Voltage	BV_{DSS}	80	-	-	V	V_{GS}=0V,I_D=250μA
Zero Gate Voltage Drain Current	I_{DSS}	-	-	1	μA	V_{DS}=80V,V_{GS}=0V
Gate-Body Leakage Current,Forward	I_{GSSF}	-	-	100	nA	V_{GS}=20V,V_{DS}=0V
Gate-Body Leakage Current,Reverse	I_{GSSR}	-	-	-100	nA	V_{GS}=-20V,V_{DS}=0V
Gate-Source Threshold Voltage	$V_{GS(th)}$	2.0	-	4.0	V	V_{DS}=V_{GS},I_D=250μA
Drain-Source On-State Resistance	$R_{DS(on)}$	-	1.7	2.2	mΩ	V_{GS}=10V,I_D=20A
Gate Resistance	R_g	-	1.6	-	Ω	V_{GS}=0V, V_{DS} Open, f=1MHz
Forward Transconductance	g_{fs}	-	18	-	S	V_{DS}=5V,I_D=20A

Dynamic characteristics

Parameter	Symbol	Values			Unit	Note/Test Conditions
		Min	Typ	Max		
Input Capacitance	C_{iss}	-	12780	-	pF	V_{DS}=25V,V_{GS}=0V,f=1.0MHZ
Output Capacitance	C_{oss}	-	3264	-	pF	V_{DS}=25V,V_{GS}=0V,f=1.0MHZ
Reverse Transfer Capacitance	C_{rss}	-	262	-	pF	V_{DS}=25V,V_{GS}=0V,f=1.0MHZ
Turn-On Delay Time	$t_{d(on)}$	-	39	-	ns	V_{DD}=42.5V,R_G=3Ω,V_{GS}=10V,I_D=10A
Turn-On Rise Time	t_r	-	122	-	ns	V_{DD}=42.5V,R_G=3Ω,V_{GS}=10V,I_D=10A
Turn-Off Delay Time	$t_{d(off)}$	-	115	-	ns	V_{DD}=42.5V,R_G=3Ω,V_{GS}=10V,I_D=10A
Turn-Off Fall Time	t_f	-	137	-	ns	V_{DD}=42.5V,R_G=3Ω,V_{GS}=10V,I_D=10A

Gate charge characteristics

Parameter	Symbol	Values			Unit	Note/Test Conditions
		Min	Typ	Max		
Total Gate Charge	Q_g	-	233.5	-	nC	V_{DS}=64V,I_D=20A,V_{GS}=10V
Gate-Source Charge	Q_{gs}	-	65.9	-	nC	V_{DS}=64V,I_D=20A,V_{GS}=10V
Gate-Drain Charge	Q_{gd}	-	62.0	-	nC	V_{DS}=64V,I_D=20A,V_{GS}=10V

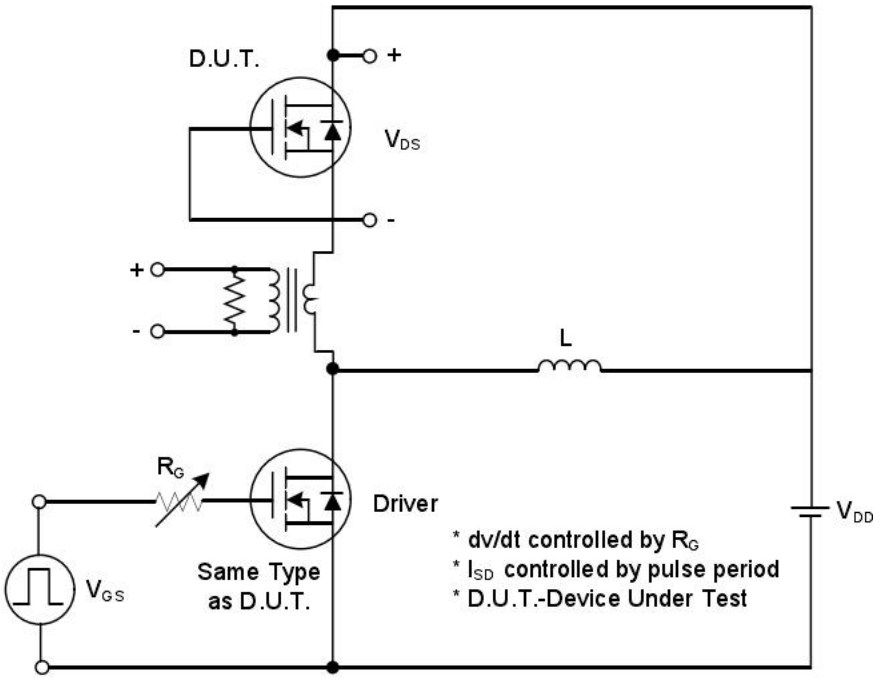
Reverse diode

Parameter	Symbol	Values			Unit	Note/Test Conditions
		Min	Typ	Max		
Continuous Diode Forward Current	I_S	-	-	180	A	-
Pulsed Diode Forward Current	I_{SM}	-	-	720	A	-
Diode Forward Voltage	V_{SD}	-	-	1.2	V	I_S=20A,V_{GS}=0V
Reverse Recovery Time	t_{rr}	-	130	-	ns	V_D=30V,I_F=1A
Reverse Recovery Charge	Q_{rr}	-	311	-	nC	di/dt=100A/μs,(Note2)

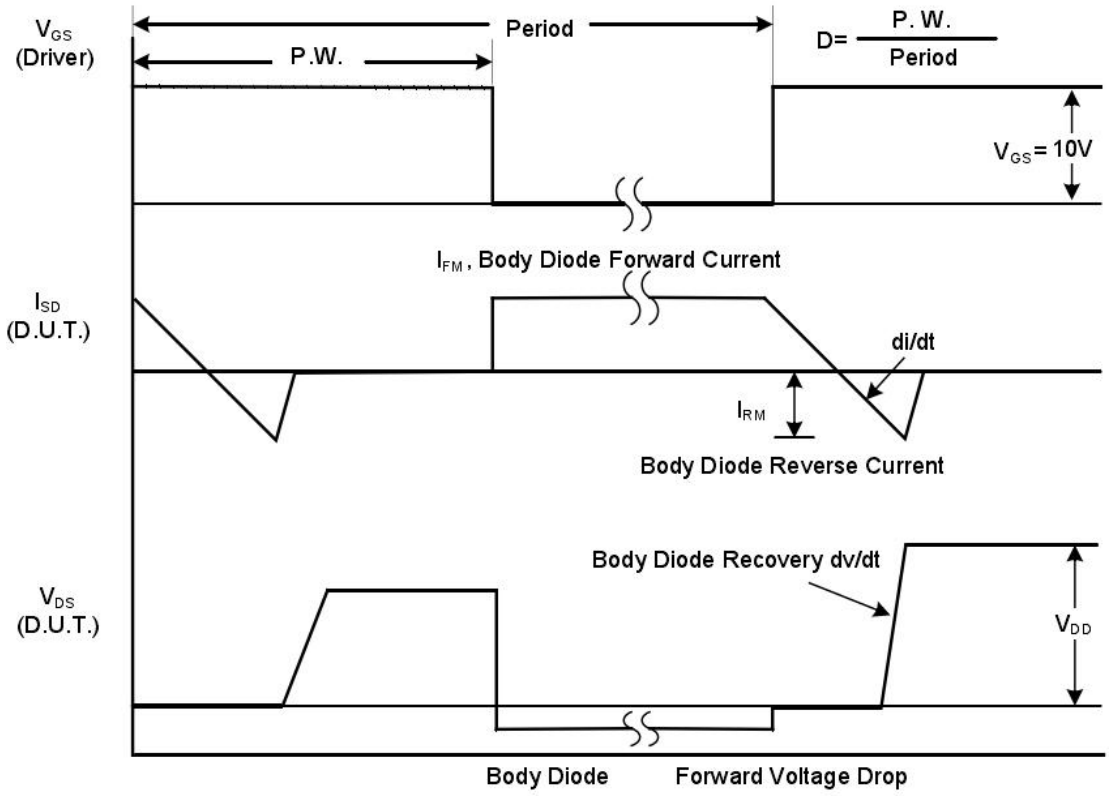
Notes

1. Repetitive Rating:pulse width limited by maximum junction temperature.
2. Pulse width≤300us,duty cycle≤2%.

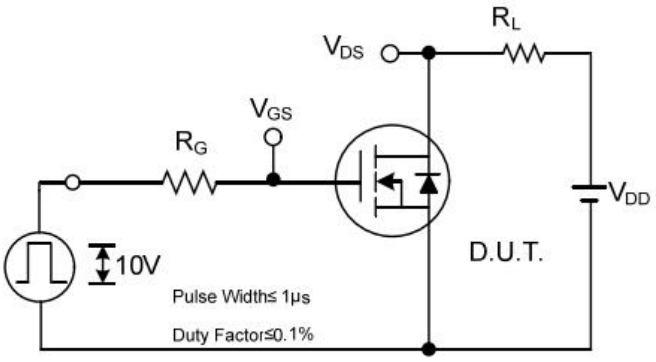
RATING AND CHARACTERISTIC CURVES



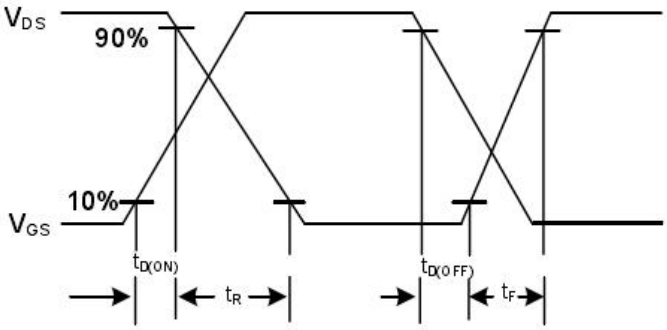
Peak Diode Recovery dv/dt Test Circuit



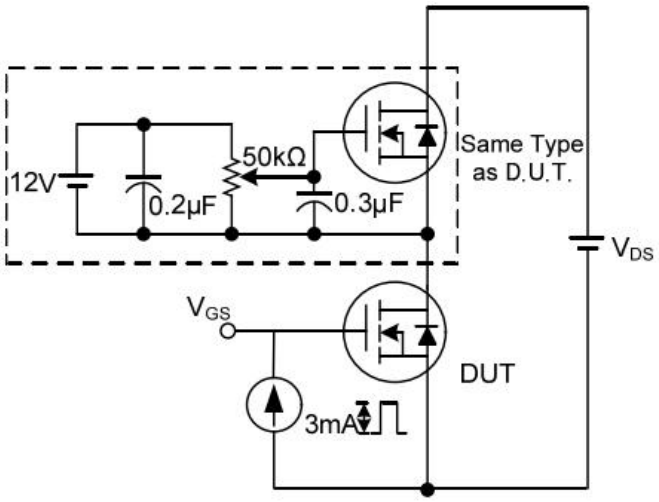
Peak Diode Recovery dv/dt Waveforms



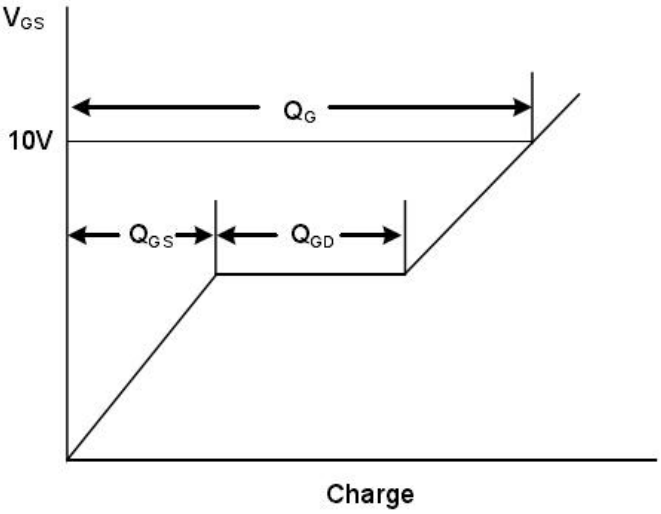
Switching Test Circuit



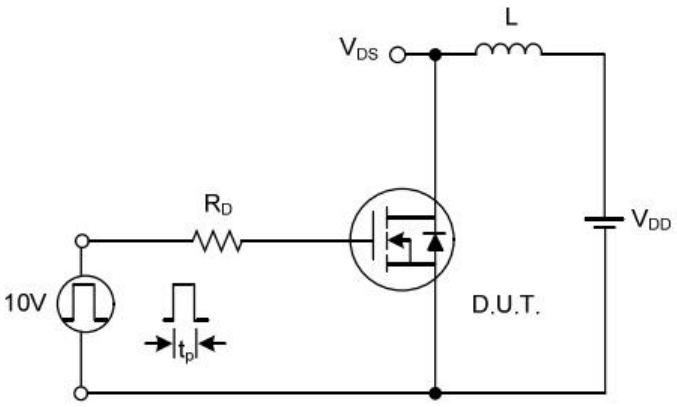
Switching Waveforms



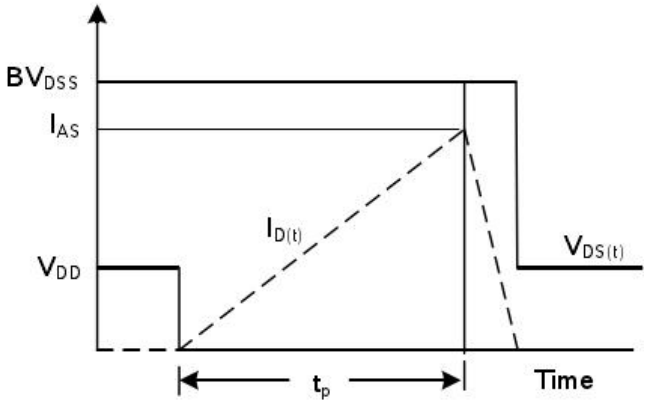
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

RATING AND CHARACTERISTIC CURVES

Figure.1 Typical Output Characteristics

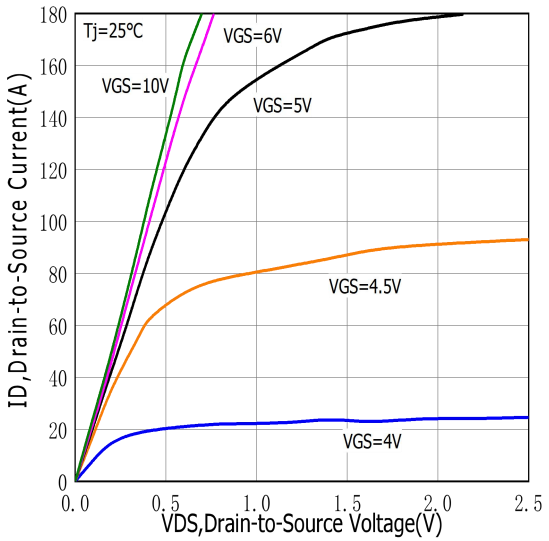


Figure.2 Typical Gate Charge vs Gate to Source Voltage

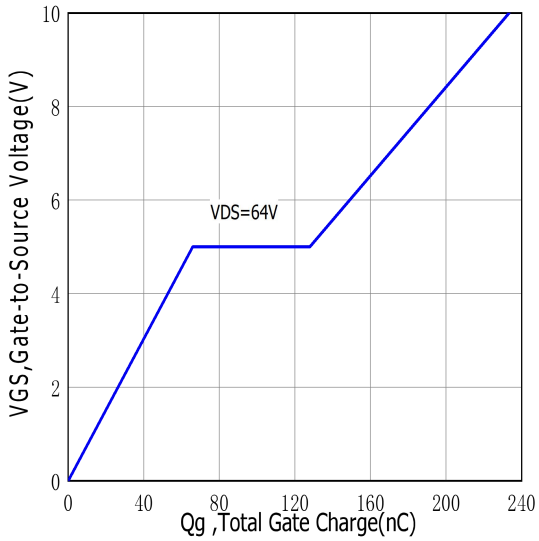


Figure.3 Typical Body Diode Transfer Characteristics

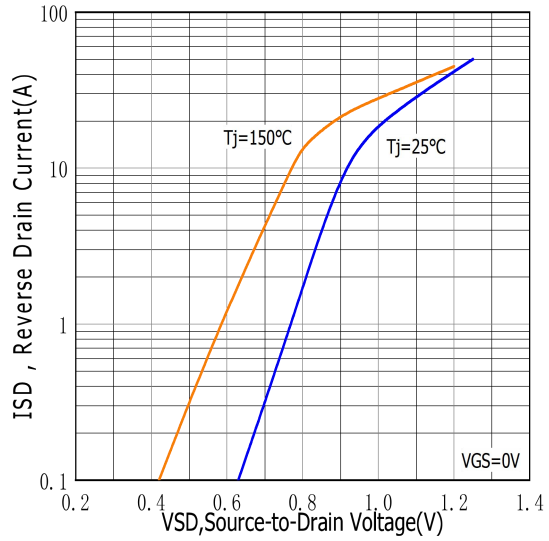


Figure.4 Typical Capacitance vs Drain to Source Voltage

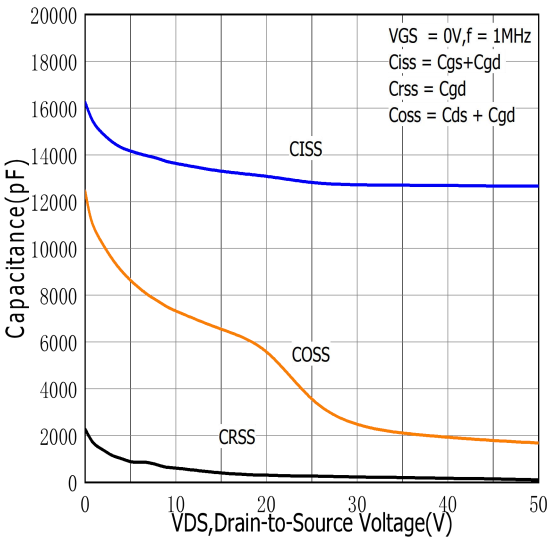


Figure.5 Typical Breakdown Voltage vs Junction Temperature

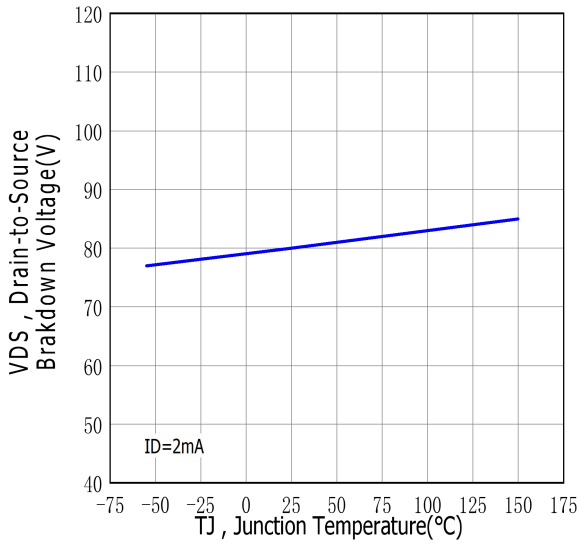


Figure.6 Typical Drain to Source on Resistance vs Junction Temperature

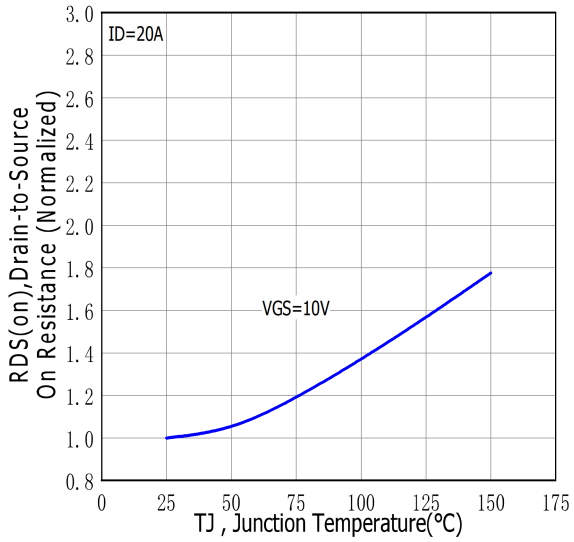


Figure.7 Maximum Forward Bias Safe Operating Area

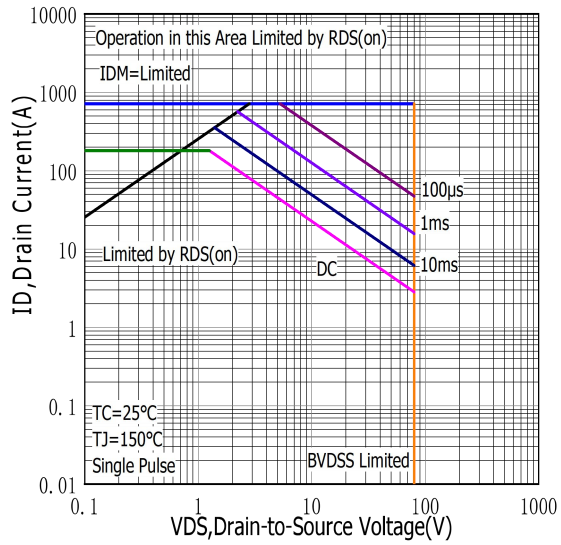


Figure.8 Typical Drain to Source ON Resistance vs Drain Current

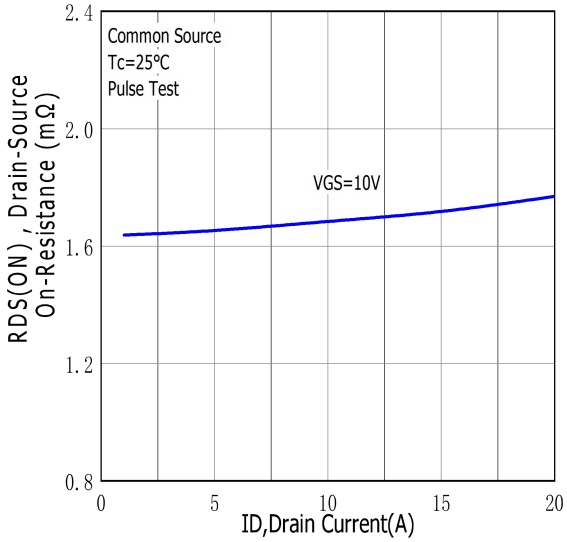


Figure.9 Maximum EAS vs Channel Temperature

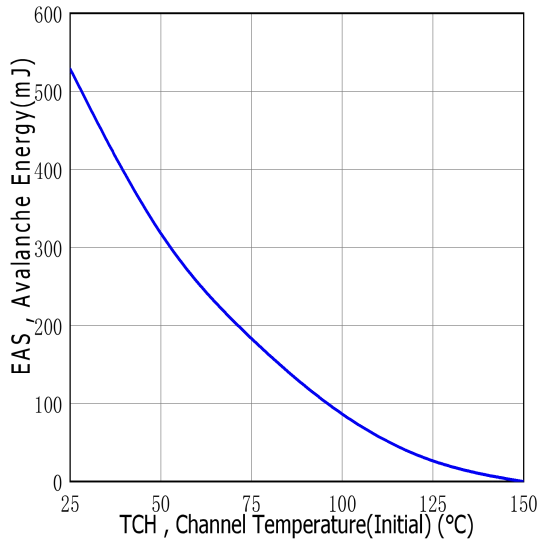


Figure.10 Typical Threshold Voltage vs Case Temperature

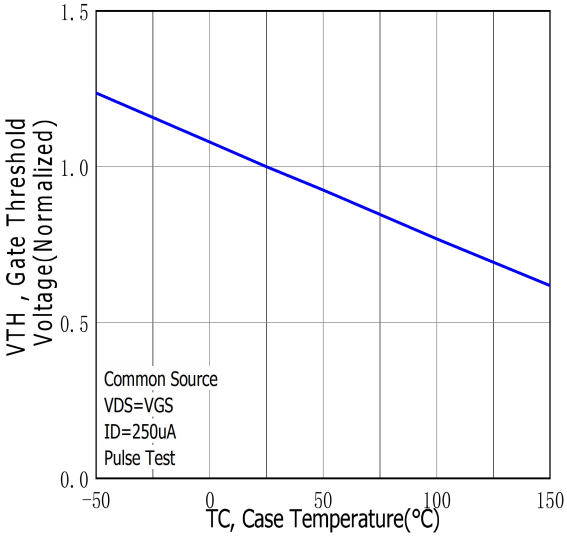


Figure.11 Typical Transfer Characteristics

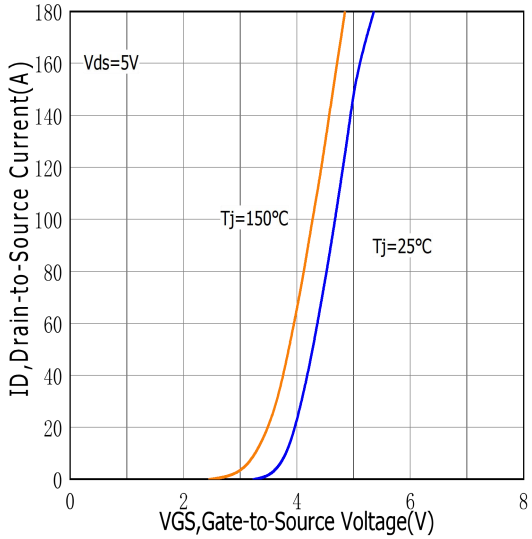


Figure.12 Maximum Power Dissipation vs Case Temperature

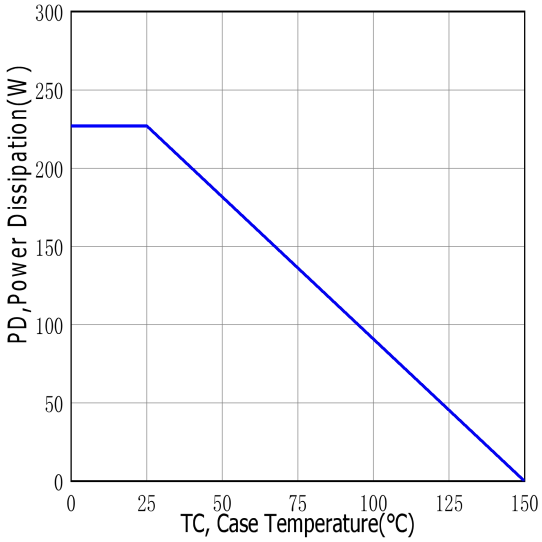
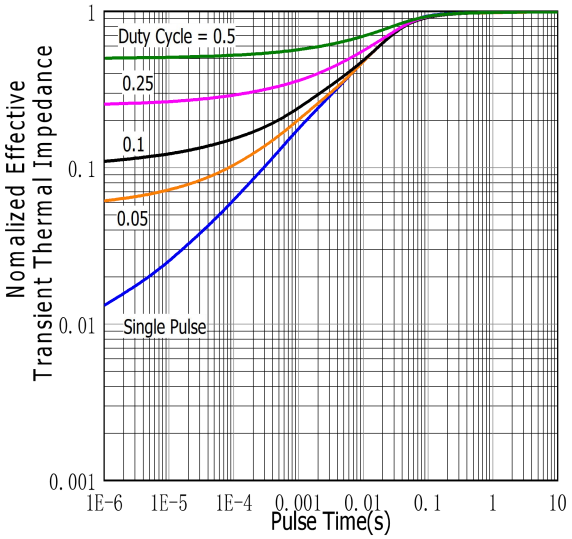
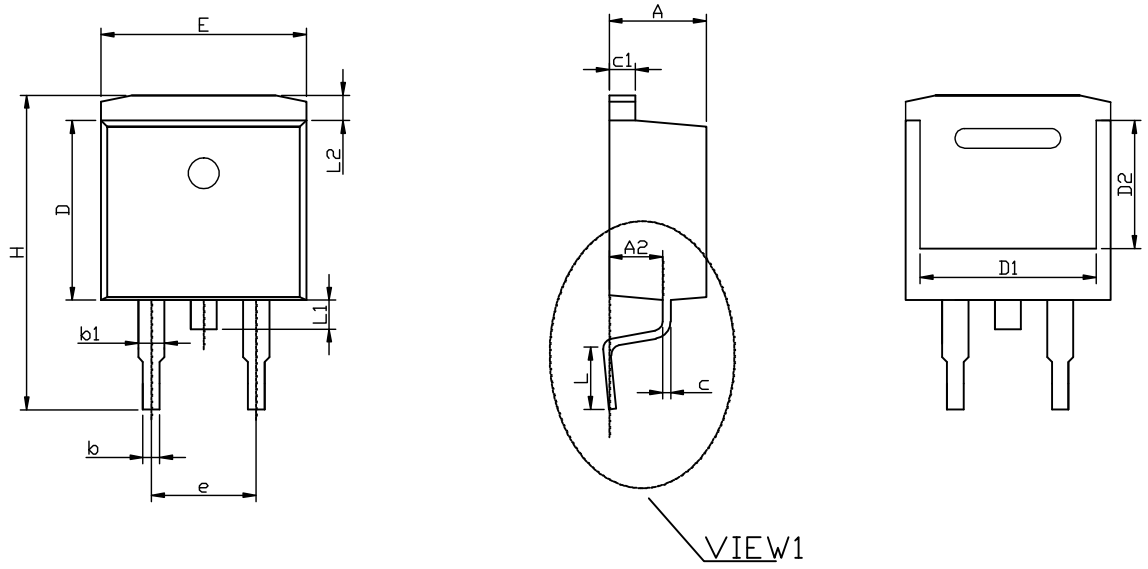


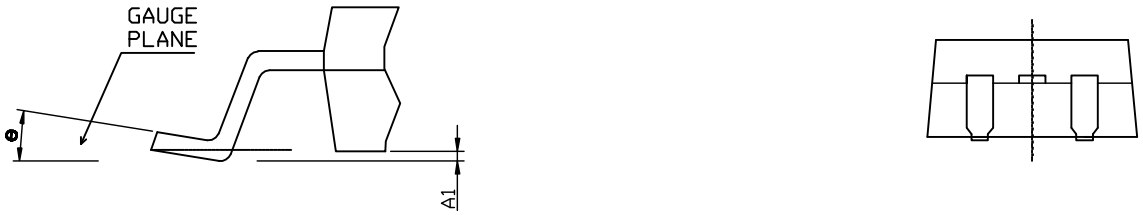
Figure.13 Maximum Effective Thermal Impedance , Junction to Case



重庆平伟实业股份有限公司
CHONGQING PINGWEI ENTERPRISE CO.,LTD

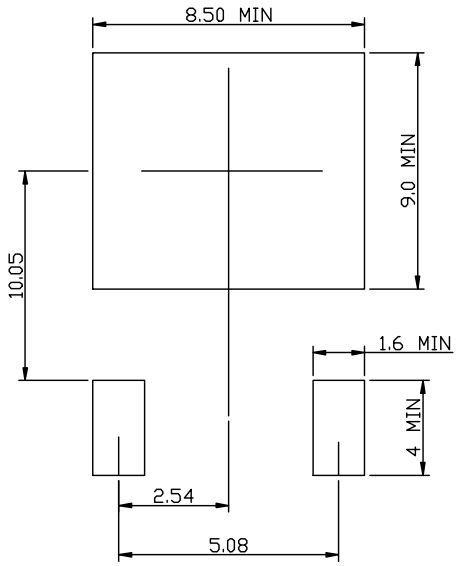
TO-263CB-2L PACKAGE OUTLINE





VIEW1

RECOMMENDED LAND PATTERN



	MIN	NOM	MAX
A	4.40	4.60	4.80
A1	0.05	0.15	0.30
A2	2.25	2.40	2.55
b	0.72	0.82	0.92
b1	1.12	1.27	1.42
c	0.40	0.50	0.60
c1	1.20	1.30	1.40
D	8.80	9.10	9.40
D1	7.75	7.95	8.15
D2	6.55	6.75	6.95
E	9.65	10.00	10.35
e		5.08BCS	
H	14.70	15.10	15.60
L	2.30	2.45	2.60
L1	1.20	1.40	1.60
L2	0.95	1.10	1.30
θ	0°	7°	8°

UNIT: mm